n-channel JFET
designed for . . .

- **VHF Amplifier**
- **Mixers**

Performance Curves NH
See Section 4

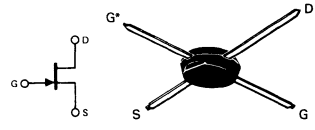
BENEFITS

- Low Noise
  NF = 3 dB Typical at 400 MHz
- Wide Band
  High g_{fs}/C_{iss} Ratio

*ABSOLUTE MAXIMUM RATINGS (25°C)

Gate-Drain or Gate Source Voltage . . . . . -30 V
Gate Current . . . . . 10 mA
Total Device Dissipation (Derate 1.4 mW/°C) . . . . . 175 mW
Operating Temperature Range . . . . . -65 to +150°C
Storage Temperature Range . . . . . -65 to +200°C
Lead Temperature
(1/16" from case for 60 seconds) . . . . . 300°C

OD-84
See Section 5



Note: G* is back Gate contact.

*ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

		Characteristic		Min	Max	Unit	Test Conditions	
1	STATIC	I_{GSS}	Gate Reverse Current		-0.1	nA	V_{GS} = -20 V, V_{DS} = 0	
2					-0.1	μA		150°C
3		BV_{GSS}	Gate-Source Breakdown Voltage	-30		V	I_G = -1 μA, V_{DS} = 0	
4		$V_{GS(off)}$	Gate-Source Cutoff Voltage		-6	V	V_{DS} = 15 V, I_D = 1 nA	
5		I_{DSS}	Saturation Drain Current (Note 1)	5	15	mA	V_{DS} = 15 V, V_{GS} = 0	
6	DYNAMIC	g_{fs}	Common-Source Forward Transconductance	4500	7500	μmho		f = 1 kHz
7		g_{os}	Common-Source Output Conductance		50	μmho		
8		C_{rss}	Common-Source Reverse Transfer Capacitance		0.8	pF		
9		C_{iss}	Common-Source Input Capacitance		3.5	pF		f = 1 MHz
10		C_{oss}	Common-Source Output Capacitance		1.3	pF		

		Characteristic		100 MHz Min	100 MHz Max	400 MHz Min	400 MHz Max	Unit	Test Conditions
11	HIGH FREQ	g_{iss}	Common-Source Input Conductance		100		1000	μmho	V_{DS} = 15 V, V_{GS} = 0
12		b_{iss}	Common-Source Input Susceptance		2000		8000		
13		g_{oss}	Common-Source Output Conductance		75		100		
14		b_{oss}	Common-Source Output Susceptance		800		3000		
15		g_{fs}	Common-Source Forward Transconductance (Note 1)			4000			
16		G_{ps}	Common-Source Power Gain	18		10		dB	V_{DS} = 15 V, I_D = 5 mA
17		NF	Noise Figure		2		4	dB	V_{DS} = 15 V, I_D = 5 mA, R_G = 1 KΩ

*JEDEC Registered Data.

NH

NOTE:

1. Pulse test duration = 300 μs.